MOSFET – Power, N-Channel 60 V, 46 A, 16 m Ω

Features

- Low Gate Charge
- Fast Switching
- High Current Capability
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parar	Symbol	Value	Unit		
Drain-to-Source Voltaç	ge		V _{DSS}	60	V
Gate-to-Source Voltag	e – Contir	nuous	V _{GS}	±20	V
Gate-to-Source Voltag - Non-Repetitive (t _p <			V_{GS}	±30	V
Continuous Drain		T _C = 25°C	I _D	46	Α
Current (R _{θJC})	Steady	T _C = 100°C		33	
Power Dissipation $(R_{\theta JC})$	State	T _C = 25°C	P_{D}	71	W
Pulsed Drain Current	t _p =	= 10 μs	I _{DM}	203	Α
Operating Junction and	T _J , T _{stg}	-55 to 175	°C		
Source Current (Body [Diode)		IS	46	Α
	Single Pulse Drain-to-Source (L =				mJ
Avalanche Energy	0.1 mH)	I _{AS}	27	Α	
Lead Temperature for S (1/8" from case for 10 s	TL	260	°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.1	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	49	

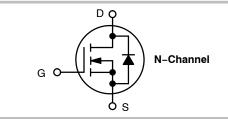
1. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.



ON Semiconductor®

http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
60 V	16 m Ω @ 10 V	46 A
00 1	19 mΩ @ 4.5 V	4074



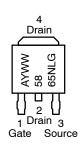


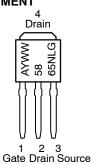
DPAK
CASE 369AA
(Surface Mount)
STYLE 2



IPAK CASE 369D (Straight Lead) STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENT





A = Assembly Location*

Y = Year

WW = Work Week 5865NL = Device Code G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_J = 25$ °C unless otherwise noted)

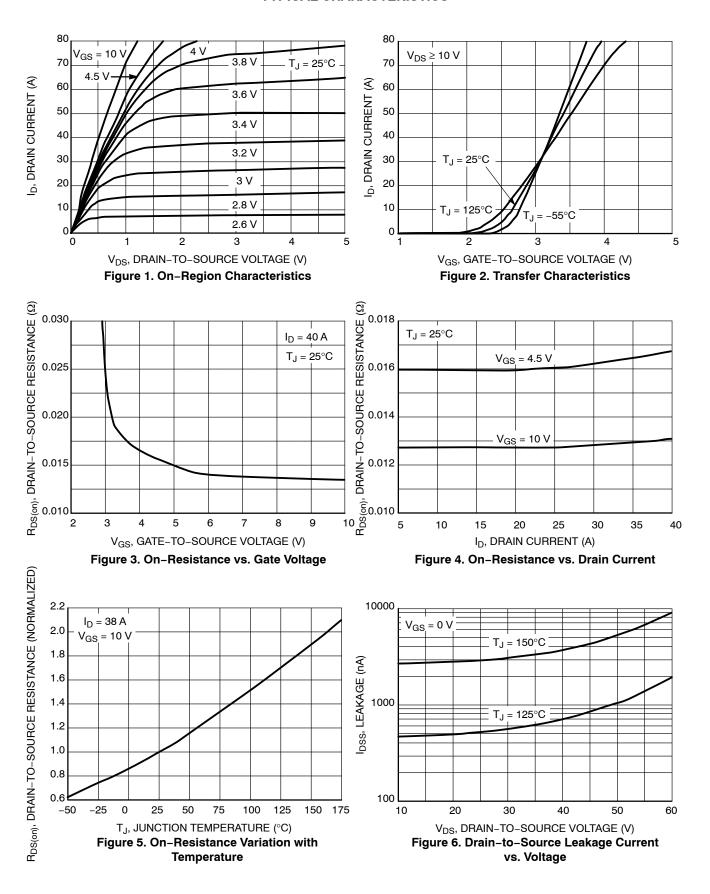
Parameter	Symbol	Test Condi	ition	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•		•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D =$: 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				55		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 60 V	$T_{J} = 25^{\circ}C$ $T_{.I} = 150^{\circ}C$			1.0	μΑ
Gate-to-Source Leakage Current	1	$V_{DS} = 00 \text{ V}$ $V_{DS} = 0 \text{ V}, V_{GS}$	· ·			100 ±100	nA
3	I _{GSS}	v _{DS} = 0 v, v _{GS}	= 120 V			±100	ПА
ON CHARACTERISTICS (Note 2)	1 v/ 1		050 4	1.0	1		1 1/
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D =$	= 250 μΑ	1.0		2.0	V
Negative Threshold Temperature Co- efficient	V _{GS(TH)} /T _J				5.6		mV/°C
Drain-to-Source on Resistance	R _{DS(on)}	V_{GS} = 10 V, I_{D}			13	16	m $Ω$
Drain-to-Source on Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_{C}$	₀ = 20 A		16	19	mΩ
Forward Transconductance	gFS	V _{DS} = 15 V, I _D = 20 A			15		S
CHARGES, CAPACITANCES AND GA	TE RESISTANCI	ES	-		-	-	-
Input Capacitance	C _{iss}				1400		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V, f} = 1$ $V_{DS} = 25$	I.0 MHz, V		137		┦ │
Reverse Transfer Capacitance	C _{rss}	*D2 - 20	•		95		
Total Gate Charge	Q _{G(TOT)}				29		nC
Threshold Gate Charge	Q _{G(TH)}	$V_{GS} = 10 \text{ V}, V_{D}$	_S = 48 V,		1.1		
Gate-to-Source Charge	Q_{GS}	$I_D = 40$	Ă		4		
Gate-to-Drain Charge	Q_{GD}				8		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = 4.5 \text{ V}, V_{D}$ $I_{D} = 40 \text{ A}$			15		nC
Gate Resistance	R_{G}				1.3		Ω
SWITCHING CHARACTERISTICS (Not	e 3)					•	•
Turn-On Delay Time	t _{d(on)}				8.4		ns
Rise Time	t _r	$V_{GS} = 10 \text{ V}, V_{DI}$	_D = 48 V,		12.4		
Turn-Off Delay Time	t _{d(off)}	$I_D = 40 \text{ A}, R_G$	= 2.5 Ω		26		
Fall Time	t _f				4.4		
DRAIN-SOURCE DIODE CHARACTER	RISTICS					•	
Forward Diode Voltage	V_{SD}	V _{GS} = 0 V,	T _J = 25°C		0.95	1.2	V
_		$I_S = 40 \text{ A}$	T _J = 125°C		0.85		1
Reverse Recovery Time	t _{RR}				20		ns
Charge Time	ta	V _{GS} = 0 V, dls/dt =	= 100 A/us.		13		1
Discharge Time	tb	$I_S = 40$			7		1
Reverse Recovery Charge	Q_{RR}				13		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

^{3.} Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

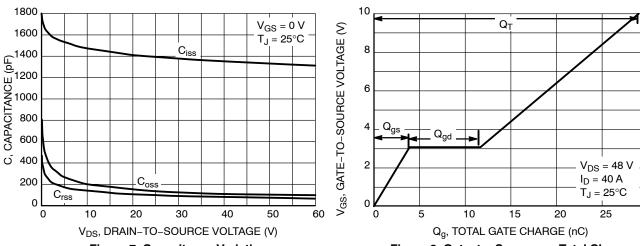


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source vs. Total Charge

30

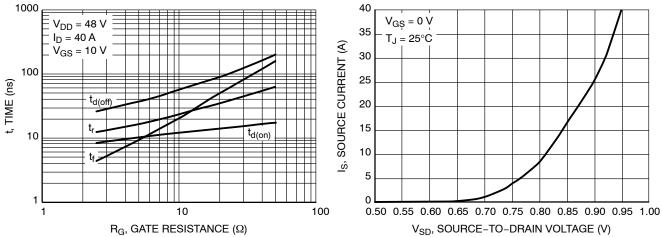


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

Figure 10. Diode Forward Voltage vs. Current

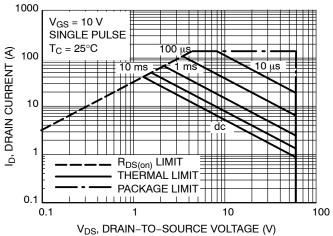


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

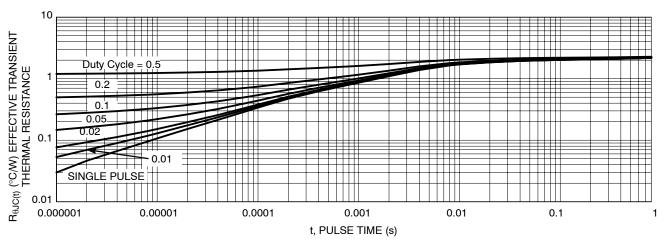


Figure 12. Thermal Response

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NTD5865NL-1G	IPAK (Straight Lead) (Pb-Free)	75 Units / Rail
NTD5865NLT4G	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

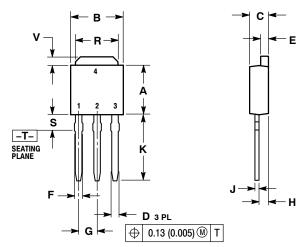


DPAK INSERTION MOUNT

CASE 369 ISSUE O

DATE 02 JAN 2000





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090	BSC	2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
٧	0.030	0.050	0.77	1.27

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		STYLE 5:		STYLE 6:	
PIN 1.	BASE	PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	GATE	PIN 1.	MT1
2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE	2.	MT2
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	GATE	3.	CATHODE	3.	GATE
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE	4.	MT2

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DESCRIPTION:	DPAK INSERTION MOUNT		PAGE 1 OF 1	

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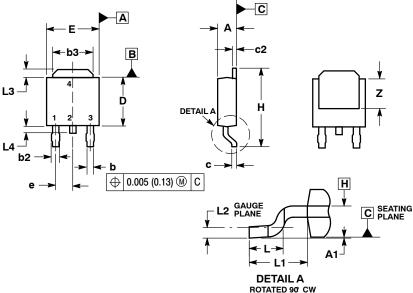
DPAK (SINGLE GUAGE) CASE 369AA **ISSUE B** SCALE 1:1 C

DATE 03 JUN 2010

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCHES.
 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	



STYLE 1: PIN 1. BASE

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE

STYLE 5:

2. COLLECTOR 3. EMITTER 4. COLLECTOR

STYLE 2: PIN 1. GATE

2. DRAIN 3. SOURCE 4. DRAIN

STYLE 3:

PIN 1. ANODE 2. CATHODE 3. ANODE CATHODE

STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE

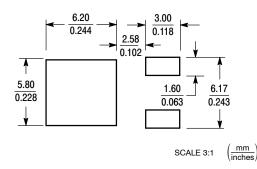
STYLE 7:

STYLE 6: PIN 1. MT1 2. MT2

3. GATE

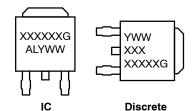
PIN 1. GATE 2. COLLECTOR 3. EMITTER COLLECTOR

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code Α = Assembly Location L = Wafer Lot ٧ = Year = Work Week WW = Pb-Free Package

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

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^{*}This information is generic. Please refer to device data sheet for actual part

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